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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

E·XEI

2000	
Product Status	Active
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-TBGA (35x35)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8347eczuajdb

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1 Overview

This section provides a high-level overview of the MPC8347E features. Figure 1 shows the major functional units within the MPC8347E.

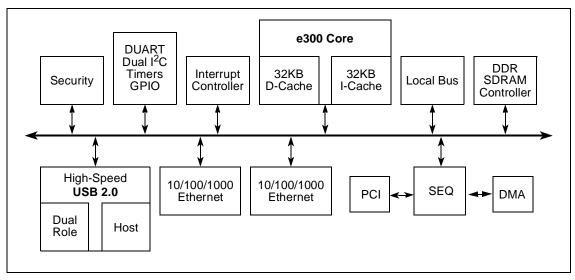


Figure 1. MPC8347E Block Diagram

Major features of the MPC8347E are as follows:

- Embedded PowerPC e300 processor core; operates at up to 667 MHz
 - High-performance, superscalar processor core
 - Floating-point, integer, load/store, system register, and branch processing units
 - 32-Kbyte instruction cache, 32-Kbyte data cache
 - Lockable portion of L1 cache
 - Dynamic power management
 - Software-compatible with the other Freescale processor families that implement Power Architecture technology
- Double data rate, DDR SDRAM memory controller
 - Programmable timing for DDR-1 SDRAM
 - 32- or 64-bit data interface, up to 333-MHz data rate for TBGA, 266 MHz for PBGA
 - Four banks of memory, each up to 1 Gbyte
 - DRAM chip configurations from 64 Mbit to 1 Gbit with x8/x16 data ports
 - Full error checking and correction (ECC) support
 - Page mode support (up to 16 simultaneous open pages)
 - Contiguous or discontiguous memory mapping
 - Read-modify-write support
 - Sleep mode for self-refresh SDRAM
 - Auto refresh

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8347E. The MPC8347E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 **Overall DC Electrical Characteristics**

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

	Characteristic	Symbol	Max Value	Unit	Notes				
Core supply voltage		V _{DD} -0.3 to 1.32		V					
PLL supply voltage		AV _{DD}	/ _{DD} –0.3 to 1.32						
DDR DRAM I/O voltag	e	GV _{DD} -0.3 to 3.63		V					
Three-speed Ethernet	I/O, MII management voltage	LV _{DD}	-0.3 to 3.63	V					
PCI, local bus, DUART, system control and power management, I ² C, and JTAG I/O voltage		OV _{DD}	-0.3 to 3.63	V					
Input voltage	DDR DRAM signals	MV _{IN}	–0.3 to (GV _{DD} + 0.3)	V	2, 5				
	DDR DRAM reference	MV _{REF}	–0.3 to (GV _{DD} + 0.3)	V	2, 5				
Three-speed Ethernet signals Local bus, DUART, CLKIN, system control and power management, I ² C, and JTAG signals		LV _{IN}	-0.3 to (LV _{DD} + 0.3)	V	4, 5				
		OV _{IN}	–0.3 to (OV _{DD} + 0.3)	V	3, 5				
	PCI	OV _{IN}	-0.3 to (OV _{DD} + 0.3)	V	6				
Storage temperature ra	ange	T _{STG}	–55 to 150	°C					

Table 1. Absolute Maximum Ratings¹

Notes:

- ¹ Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
- ² Caution: MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ³ Caution: OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ⁴ Caution: LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ⁵ (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
- ⁶ OV_{IN} on the PCI interface can overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Supply Voltage Specification

Table 2 provides the recommended operating conditions for the MPC8347E. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V _{DD}	1.2 V ± 60 mV	V	1
PLL supply voltage	AV _{DD}	1.2 V ± 60 mV	V	1
DDR DRAM I/O supply voltage	GV _{DD}	2.5 V ± 125 mV	V	
Three-speed Ethernet I/O supply voltage	LV _{DD1}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	
Three-speed Ethernet I/O supply voltage	LV _{DD2}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	
PCI, local bus, DUART, system control and power management, I ² C, and JTAG I/O voltage	OV _{DD}	3.3 V ± 330 mV	V	

Note:

¹ GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8347E.

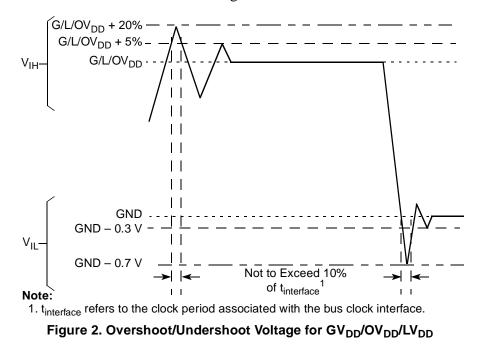


Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8347E for the 3.3-V signals, respectively.

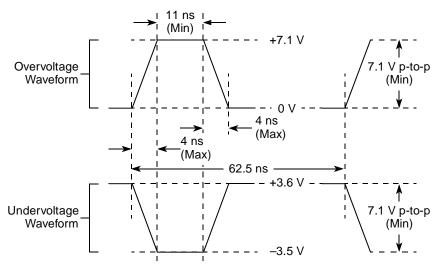


Figure 3. Maximum AC Waveforms on PCI Interface for 3.3-V Signaling

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	40	OV _{DD} = 3.3 V
PCI signals (not including PCI output clocks)	25	
PCI output clocks (including PCI_SYNC_OUT)	40	
DDR signal	18	GV _{DD} = 2.5 V
TSEC/10/100 signals	40	LV _{DD} = 2.5/3.3 V
DUART, system control, I ² C, JTAG, USB	40	OV _{DD} = 3.3 V
GPIO signals	40	OV _{DD} = 3.3 V, LV _{DD} = 2.5/3.3 V

Table 3. Output Drive Capability

2.2 Power Sequencing

MPC8347E does not require the core supply voltage and I/O supply voltages to be applied in any particular order. Note that during the power ramp up, before the power supplies are stable, there may be a period of time that I/O pins are actively driven. After the power is stable, as long as **PORESET** is asserted, most I/O pins are three-stated. To minimize the time that I/O pins are actively driven, it is recommended to apply core voltage before I/O voltage and assert **PORESET** before the power supplies fully ramp up.

8 Ethernet: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speeds (10/100/1000 Mbps) and MII management.

8.1 Three-Speed Ethernet Controller (TSEC)— GMII/MII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to the gigabit media independent interface (GMII), the media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), and reduced ten-bit interface (RTBI) signals except management data input/output (MDIO) and management data clock (MDC). The MII, GMII, and TBI interfaces are defined for 3.3 V, and the RGMII and RTBI interfaces are defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard *Reduced Pin-Count Interface for Gigabit Ethernet Physical Layer Device Specification*, Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, "Ethernet Management Interface Electrical Characteristics."

8.1.1 **TSEC DC Electrical Characteristics**

GMII, MII, TBI, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 19 and Table 20. The RGMII and RTBI signals in Table 20 are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Parameter	Symbol	Conditions		Min	Мах	Unit
Supply voltage 3.3 V	LV _{DD} ²	—		2.97	3.63	V
Output high voltage	V _{OH}	I _{OH} = -4.0 mA	LV _{DD} = Min	2.40	LV _{DD} + 0.3	V
Output low voltage	V _{OL}	$I_{OL} = 4.0 \text{ mA}$ $LV_{DD} = Min$		GND	0.50	V
Input high voltage	V _{IH}			2.0	LV _{DD} + 0.3	V
Input low voltage	V _{IL}	—	_	-0.3	0.90	V
Input high current	IIH	$V_{IN}^{1} = LV_{DD}$		—	40	μΑ
Input low current	۱ _{IL}	V _{IN} ¹ =	GND	-600	—	μΑ

Table 19. GMII/TBI and MII DC Electrical Characteristics

Notes:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

2. GMII/MII pins not needed for RGMII or RTBI operation are powered by the $\ensuremath{\mathsf{OV}_{\mathsf{DD}}}$ supply.

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV _{DD}	—		2.37	2.63	V
Output high voltage	V _{OH}	$I_{OH} = -1.0 \text{ mA}$ $LV_{DD} = Min$		2.00	LV _{DD} + 0.3	V
Output low voltage	V _{OL}	$I_{OL} = 1.0 \text{ mA}$ $LV_{DD} = Min$		GND – 0.3	0.40	V
Input high voltage	V _{IH}	— LV _{DD} = Min		1.7	LV _{DD} + 0.3	V
Input low voltage	V _{IL}	—	LV _{DD} = Min	-0.3	0.70	V
Input high current	I _{IH}	$V_{IN}^{1} = LV_{DD}$		—	10	μA
Input low current	۱ _{IL}	V _{IN} ¹ =	GND	-15	—	μΑ

Table 20. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Note:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2 GMII, MII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

8.2.1.1 GMII Transmit AC Timing Specifications

Table 21 provides the GMII transmit AC timing specifications.

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
GTX_CLK clock period	t _{GTX}	_	8.0	—	ns
GTX_CLK duty cycle	t _{GTXH} /t _{GTX}	43.75		56.25	%
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t _{GTKHDX}	0.5		5.0	ns
GTX_CLK clock rise time, V _{IL} (min) to V _{IH} (max)	t _{GTXR}	_		1.0	ns
GTX_CLK clock fall time, V _{IH} (max) to V _{IL} (min)	t _{GTXF}	_		1.0	ns
GTX_CLK125 clock period	t _{G125} 2	_	8.0	—	ns
GTX_CLK125 reference clock duty cycle measured at $LV_{DD}/2$	t _{G125H} /t _{G125}	45		55	%

Notes:

1. The symbols for timing specifications follow the pattern t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

2. This symbol represents the external GTX_CLK125 signal and does not follow the original symbol naming convention.

Table 21. GMII Transmit AC Timing Specifications

Table 35. Local Bus General Timing Parameters—DLL Bypass ⁹ (continued)

Parameter	Symbol ¹	Min	Мах	Unit	Notes
Local bus clock to output valid	t _{LBKLOV}	_	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t _{LBKHOZ}	_	4	ns	8

Notes:

- The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
 </sub>
- 2. All timings are in reference to the falling edge of LCLK0 (for all outputs and for LGTA and LUPWAIT inputs) or the rising edge of LCLK0 (for all other inputs).
- 3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
- 4. Input timings are measured at the pin.
- 5. t_{LBOTOT1} should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
- 6. t_{LBOTOT2} should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.the
- 7. t_{LBOTOT3} should be used when RCWH[LALE] is set and when the load on the LALE output pin equals to the load on the LAD output pins.
- 8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

Figure 19 provides the AC test load for the local bus.

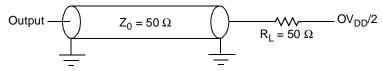


Figure 19. Local Bus C Test Load

Local Bus

Figure 20 through Figure 25 show the local bus signals.

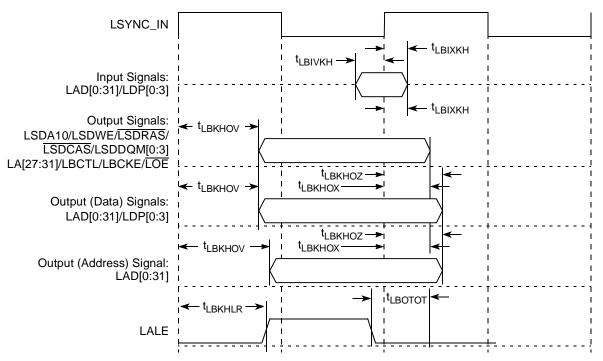


Figure 20. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

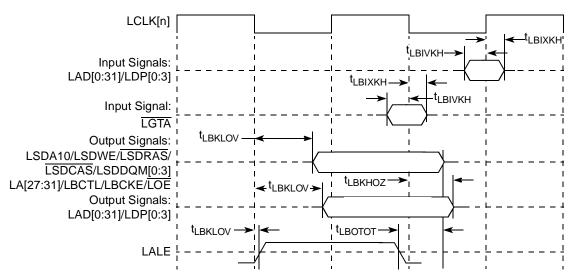


Figure 21. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

Table 37. JTAG AC Timing Specifications (Independent of CLKIN)¹ (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Мах	Unit	Notes
Output hold times: Boundary-scan data TDO	^t jtkldx ^t jtklox	2 2		ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	^t jtkldz ^t jtkloz	2 2	19 9	ns	5, 6

Notes:

- 1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 26). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
- 2. The symbols for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}}
- 3. TRST is an asynchronous level sensitive signal. The setup time is for test purposes only.
- 4. Non-JTAG signal input timing with respect to t_{TCLK}.
- 5. Non-JTAG signal output timing with respect to t_{TCLK} .
- 6. Guaranteed by design and characterization.

Figure 26 provides the AC test load for TDO and the boundary-scan outputs of the MPC8347E.

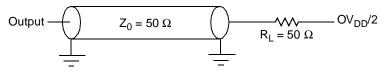


Figure 26. AC Test Load for the JTAG Interface

Figure 27 provides the JTAG clock input timing diagram.

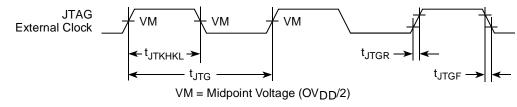


Figure 27. JTAG Clock Input Timing Diagram

Timers

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the MPC8347E timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Characteristic	Symbol	Condition	Min	Мах	Unit
Input high voltage	V _{IH}		2.0	OV _{DD} + 0.3	V
Input low voltage	V _{IL}		-0.3	0.8	V
Input current	I _{IN}			±5	μA
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	—	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V

Table 43. Timer DC Electrical Characteristics

14.2 Timer AC Timing Specifications

Table 44 provides the timer input and output AC timing specifications.

Table 44. Timers Input AC Timing Specifications¹

Characteristic	Symbol ²	Min	Unit
Timers inputs—minimum pulse width	t _{TIWID}	20	ns

Notes:

1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.

2. Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by external synchronous logic. Timer inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

15 GPIO

This section describes the DC and AC electrical specifications for the GPIO.

15.1 GPIO DC Electrical Characteristics

Table 45 provides the DC electrical characteristics for the MPC8347E GPIO.

Table 45. GPIO DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V _{IH}		2.0	OV _{DD} + 0.3	V
Input low voltage	V _{IL}		-0.3	0.8	V
Input current	I _{IN}			±5	μΑ
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	—	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V

15.2 GPIO AC Timing Specifications

Table 46 provides the GPIO input and output AC timing specifications.

Table 46. GPIO Input AC Timing Specifications¹

Characteristic	Symbol ²	Min	Unit
GPIO inputs—minimum pulse width	t _{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.

 GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by external synchronous logic. GPIO inputs must be valid for at least t_{PIWID} ns to ensure proper operation.

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LBCTL	AN26	0	OV _{DD}	
LALE	AK24	0	OV _{DD}	
LGPL0/LSDA10/cfg_reset_source0	AP27	I/O	OV _{DD}	
LGPL1/LSDWE/cfg_reset_source1	AL25	I/O	OV _{DD}	
LGPL2/LSDRAS/LOE	AJ24	0	OV _{DD}	
LGPL3/LSDCAS/cfg_reset_source2	AN27	I/O	OV _{DD}	
LGPL4/LGTA/LUPWAIT/LPBSE	AP28	I/O	OV _{DD}	
LGPL5/cfg_clkin_div	AL26	I/O	OV _{DD}	
LCKE	AM27	0	OV _{DD}	
LCLK[0:2]	AN28, AK26, AP29	0	OV _{DD}	
LSYNC_OUT	AM12	0	OV _{DD}	
LSYNC_IN	AJ10	I	OV _{DD}	
	General Purpose I/O Timers	-		-
GPIO1[0]/GTM1_TIN1/GTM2_TIN2	F24	I/O	OV _{DD}	
GPIO1[1]/GTM1_TGATE1/GTM2_TGATE2	E24	I/O	OV _{DD}	
GPIO1[2]/GTM1_TOUT1	B25	I/O	OV _{DD}	
GPIO1[3]/GTM1_TIN2/GTM2_TIN1	D24	I/O	OV _{DD}	
GPIO1[4]/GTM1_TGATE2/GTM2_TGATE1	A25	I/O	OV _{DD}	
GPIO1[5]/GTM1_TOUT2/GTM2_TOUT1	B24	I/O	OV _{DD}	
GPIO1[6]/GTM1_TIN3/GTM2_TIN4	A24	I/O	OV _{DD}	
GPIO1[7]/GTM1_TGATE3/GTM2_TGATE4	D23	I/O	OV _{DD}	
GPIO1[8]/GTM1_TOUT3	B23	I/O	OV _{DD}	
GPIO1[9]/GTM1_TIN4/GTM2_TIN3	A23	I/O	OV _{DD}	
GPIO1[10]/GTM1_TGATE4/GTM2_TGATE3	F22	I/O	OV _{DD}	
GPIO1[11]/GTM1_TOUT4/GTM2_TOUT3	E22	I/O	OV _{DD}	
	USB Port 1			
MPH1_D0_ENABLEN/DR_D0_ENABLEN	A26	I/O	OV _{DD}	
MPH1_D1_SER_TXD/DR_D1_SER_TXD	B26	I/O	OV _{DD}	
MPH1_D2_VMO_SE0/DR_D2_VMO_SE0	D25	I/O	OV _{DD}	
MPH1_D3_SPEED/DR_D3_SPEED	A27	I/O	OV _{DD}	
MPH1_D4_DP/DR_D4_DP	B27	I/O	OV _{DD}	
MPH1_D5_DM/DR_D5_DM	C27	I/O	OV _{DD}	
MPH1_D6_SER_RCV/DR_D6_SER_RCV	D26	I/O	OV _{DD}	
MPH1_D7_DRVVBUS/DR_D7_DRVVBUS	E26	I/O	OV _{DD}	T

Table 51. MPC8347E (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
	No Connection			
NC	W32, AA31, AA32, AA33, AA34, AB31, AB32, AB33, AB34, AC29, AC31, AC33, AC34, AD30, AD32, AD33, AD34, AE29, AE30, AH32, AH33, AH34, AM33, AJ31, AJ32, AJ33, AJ34, AK32, AK33, AK34, AM34, AL33, AL34, AK31, AH30, AC32, AE32, AH31, AL32, AG34, AE33, AF32, AE34, AF34, AF33, AG33, AG32, AL11, AM11, AP10, Y32, Y34, Y31, Y33	_	_	

Table 51. MPC8347E (TBGA) Pinout Listing (continued)

Notes:

- 1. This pin is an open-drain signal. A weak pull-up resistor (1 k Ω) should be placed on this pin to OV_{DD}.
- 2. This pin is an open-drain signal. A weak pull-up resistor (2–10 k Ω) should be placed on this pin to OV_{DD}.
- 3. During reset, this output is actively driven rather than three-stated.
- 4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
- 5. This pin should have a weak pull-up if the chip is in PCI host mode. Follow the PCI specifications.
- 6. This pin must always be tied to GND.
- 7. This pin must always be pulled up to OV_{DD} .
- 8. This pin must always be left not connected.
- 9. Thermal sensitive resistor.
- 10.It is recommended that MDIC0 be tied to GRD using an 18 Ω resistor and MDIC1 be tied to DDR power using an 18 Ω resistor.
- 11.TSEC1_TXD[3] is required an external pull-up resistor. For proper functionality of the device, this pin must be pulled up or actively driven high during a hard reset. No external pull-down resistors are allowed to be attached to this net.

Table 52 provides the pinout listing for the MPC8347E, 620 PBGA package.

Table 52. MPC8347E (PBGA) Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
	PCI			
PCI1_INTA/IRQ_OUT	D20	0	OV _{DD}	2
PCI1_RESET_OUT	B21	0	OV _{DD}	
PCI1_AD[31:0]	E19, D17, A16, A18, B17, B16, D16, B18, E17, E16, A15, C16, D15, D14, C14, A12, D12, B11, C11, E12, A10, C10, A9, E11, E10, B9, B8, D9, A8, C9, D8, C8	I/O	OV _{DD}	
PCI1_C/BE[3:0]	A17, A14, A11, B10	I/O	OV _{DD}	
PCI1_PAR	D13	I/O	OV _{DD}	
PCI1_FRAME	B14	I/O	OV _{DD}	5
PCI1_TRDY	A13	I/O	OV _{DD}	5

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MCAS	AG6	0	GV _{DD}	
MCS[0:3]	AE7, AH7, AH4, AF2	0	GV _{DD}	
MCKE[0:1]	AG23, AH23	0	GV _{DD}	3
MCK[0:5]	AH15, AE24, AE2, AF14, AE23, AD3	0	GV _{DD}	
MCK[0:5]	AG15, AD23, AE3, AG14, AF24, AD2	0	GV _{DD}	
(The	Pins Reserved for Future DDR2 ey should be left unconnected for MPC834	7)		1
MODT[0:3]	AG5, AD4, AH6, AF4	_	_	
MBA[2]	AD22			
SPARE1	AF12	_	_	7
SPARE2	AG11	_	_	6
	Local Bus Controller Interface			
LAD[0:31]	T4, T5, T1, R2, R3, T2, R1, R4, P1, P2, P3, P4, N1, N4, N2, N3, M1, M2, M3, N5, M4, L1, L2, L3, K1, M5, K2, K3, J1, J2, L5, J3	I/O	OV _{DD}	
LDP[0]/CKSTOP_OUT	H1	I/O	OV _{DD}	
LDP[1]/CKSTOP_IN	К5	I/O	OV _{DD}	
LDP[2]	H2	I/O	OV _{DD}	
LDP[3]	G1	I/O	OV _{DD}	
LA[27:31]	J4, H3, G2, F1, G3	0	OV _{DD}	
LCS[0:3]	J5, H4, F2, E1	0	OV _{DD}	
LWE[0:3]/LSDDQM[0:3]/LBS[0:3]	F3, G4, D1, E2	0	OV _{DD}	
LBCTL	H5	0	OV _{DD}	
LALE	E3	0	OV _{DD}	
LGPL0/LSDA10/cfg_reset_source0	F4	I/O	OV _{DD}	
LGPL1/LSDWE/cfg_reset_source1	D2	I/O	OV _{DD}	
LGPL2/LSDRAS/LOE	C1	0	OV _{DD}	
LGPL3/LSDCAS/cfg_reset_source2	C2	I/O	OV _{DD}	
LGPL4/LGTA/LUPWAIT/LPBSE	C3	I/O	OV _{DD}	
LGPL5/cfg_clkin_div	В3	I/O	OV _{DD}	
LCKE	E4	0	OV _{DD}	
LCLK[0:2]	D4, A3, C4	0	OV _{DD}	
LSYNC_OUT	U3	0	OV _{DD}	
LSYNC_IN	Y2	I	OV _{DD}	

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MPH0_D2_VMO_SE0/DR_D10_DPPD	B24	I/O	OV _{DD}	
MPH0_D3_SPEED/DR_D11_DMMD	A24	I/O	OV _{DD}	
MPH0_D4_DP/DR_D12_VBUS_VLD	D23	I/O	OV _{DD}	
MPH0_D5_DM/DR_D13_SESS_END	C23	I/O	OV _{DD}	
MPH0_D6_SER_RCV/DR_D14	B23	I/O	OV _{DD}	
MPH0_D7_DRVVBUS/DR_D15_IDPULLUP	A23	I/O	OV _{DD}	
MPH0_NXT/DR_RX_ACTIVE_ID	D22	I	OV _{DD}	
MPH0_DIR_DPPULLUP/DR_RESET	C22	I/O	OV _{DD}	
MPH0_STP_SUSPEND/DR_TX_READY	B22	I/O	OV _{DD}	
MPH0_PWRFAULT/DR_RX_VALIDH	A22	I	OV _{DD}	
MPH0_PCTL0/DR_LINE_STATE0	E21	I/O	OV _{DD}	
MPH0_PCTL1/DR_LINE_STATE1	D21	I/O	OV _{DD}	
MPH0_CLK/DR_RX_VALID	C21	I	OV _{DD}	
Р	rogrammable Interrupt Controller			
MCP_OUT	E8	0	OV _{DD}	2
IRQ0/MCP_IN/GPIO2[12]	J28	I/O	OV _{DD}	
IRQ[1:5]/GPIO2[13:17]	K25, J25, H26, L24, G27	I/O	OV _{DD}	
IRQ[6]/GPIO2[18]/CKSTOP_OUT	G28	I/O	OV _{DD}	
IRQ[7]/GPIO2[19]/CKSTOP_IN	J26	I/O	OV _{DD}	
	Ethernet Management Interface			
EC_MDC	Y24	0	LV _{DD1}	
EC_MDIO	Y25	I/O	LV _{DD1}	2
	Gigabit Reference Clock	- 1	1	
EC_GTX_CLK125	Y26	I	LV _{DD1}	
Three-Spe	ed Ethernet Controller (Gigabit Ether	net 1)	1	
TSEC1_COL/GPIO2[20]	M26	I/O	OV _{DD}	
TSEC1_CRS/GPIO2[21]	U25	I/O	LV _{DD1}	
TSEC1_GTX_CLK	V24	0	LV _{DD1}	3
TSEC1_RX_CLK	U26	I	LV _{DD1}	
TSEC1_RX_DV U24 I		I	LV _{DD1}	
TSEC1_RX_ER/GPIO2[26]	L28 I/O OV _{DD}			
TSEC1_RXD[7:4]/GPIO2[22:25]	M27, M28, N26, N27	I/O	OV _{DD}	
TSEC1_RXD[3:0]	W26, W24, Y28, Y27	I	LV _{DD1}	
TSEC1_TX_CLK	N25	I	OV _{DD}	

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MVREF1	AF19	I	DDR reference voltage	
MVREF2	AE10	I	DDR reference voltage	
	No Connection			
NC	V1, V2, V5			

Notes:

- 1. This pin is an open-drain signal. A weak pull-up resistor (1 k Ω) should be placed on this pin to OV_{DD}.
- 2. This pin is an open-drain signal. A weak pull-up resistor (2–10 k Ω) should be placed on this pin to OV_{DD}.
- 3. During reset, this output is actively driven rather than three-stated.
- 4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
- 5. This pin should have a weak pull-up if the chip is in PCI host mode. Follow the PCI specifications.
- 6. This pin must always be tied to GND.
- 7. This pin must always be left not connected.
- 8. Thermal sensitive resistor.
- 9. It is recommended that MDIC0 be tied to GRD using an 18 Ω resistor and MDIC1 be tied to DDR power using an 18 Ω resistor.
- 10.TSEC1_TXD[3] is required an external pull-up resistor. For proper functionality of the device, this pin must be pulled up or actively driven high during a hard reset. No external pull-down resistors are allowed to be attached to this net.

Clocking

19 Clocking

Figure 41 shows the internal distribution of the clocks.

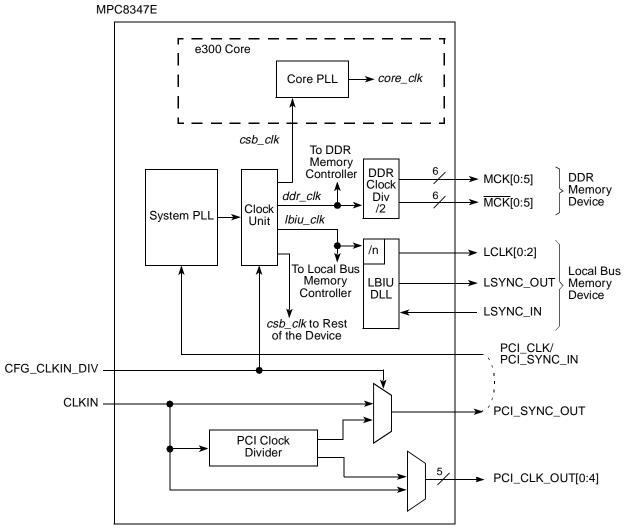


Figure 41. MPC8347E Clock Subsystem

The primary clock source can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. When the MPC8347E is configured as a PCI host device, CLKIN is its primary input clock. CLKIN feeds the PCI clock divider (÷2) and the multiplexors for PCI_SYNC_OUT and PCI_CLK_OUT. The CFG_CLKIN_DIV configuration input selects whether CLKIN or CLKIN/2 is driven out on the PCI_SYNC_OUT signal. The OCCR[PCICD*n*] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUT n signals.

PCI_SYNC_OUT is connected externally to PCI_SYNC_IN to allow the internal clock subsystem to synchronize to the system PCI clocks. PCI_SYNC_OUT must be connected properly to PCI_SYNC_IN, with equal delay to all PCI agent devices in the system, to allow the MPC8347E to function. When the MPC8347E is configured as a PCI agent device, PCI_CLK is the primary input clock and the CLKIN signal should be tied to GND.

20 Thermal

This section describes the thermal specifications of the MPC8347E.

20.1 Thermal Characteristics

Table 61 provides the package thermal characteristics for the $672 \ 35 \times 35 \ \text{mm}$ TBGA of the MPC8347E.

Characteristic	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection on single-layer board (1s)	R _{θJA}	14	°C/W	1, 2
Junction-to-ambient natural convection on four-layer board (2s2p)	R _{θJMA}	11	°C/W	1, 3
Junction-to-ambient (@ 200 ft/min) on single-layer board (1s)	R _{θJMA}	11	°C/W	1, 3
Junction-to-ambient (@ 200 ft/min) on four-layer board (2s2p)	R _{θJMA}	8	°C/W	1, 3
Junction-to-ambient (@ 2 m/s) on single-layer board (1s)	R _{θJMA}	9	°C/W	1, 3
Junction-to-ambient (@ 2 m/s) on four-layer board (2s2p)	R _{θJMA}	7	°C/W	1, 3
Junction-to-board thermal	R _{θJB}	3.8	°C/W	4
Junction-to-case thermal	R _{θJC}	1.7	°C/W	5
Junction-to-package natural convection on top	ΨJT	1	°C/W	6

Table 61. Package Thermal Characteristics for TBGA

Notes:

- 1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
- 3. Per JEDEC JESD51-6 with the board horizontal, 1 m/s is approximately equal to 200 linear feet per minute (LFM).
- 4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- 6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

Table 62 provides the package thermal characteristics for the 620 29×29 mm PBGA of the MPC8347E.

Table 62. Package Thermal Characteristics for PBGA

Characteristic	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection on single-layer board (1s)	R _{θJA}	21	°C/W	1, 2
Junction-to-ambient natural convection on four-layer board (2s2p)	R _{θJMA}	15	°C/W	1, 3
Junction-to-ambient (@ 200 ft/min) on single-layer board (1s)	R _{θJMA}	17	°C/W	1, 3
Junction-to-ambient (@ 200 ft/min) on four-layer board (2s2p)	R _{θJMA}	12	°C/W	1, 3
Junction-to-board thermal	R _{θJB}	6	°C/W	4

21.3 Decoupling Recommendations

Due to large address and data buses and high operating frequencies, the MPC8347E can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8347E system, and the MPC8347E itself requires a clean, tightly regulated source of power. Therefore, the system designer should place at least one decoupling capacitor at each V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} pin of the MPC8347E. These capacitors should receive their power from separate V_{DD} , OV_{DD} , GV_{DD} , GV_{DD} , LV_{DD} , and GND power planes in the PCB, with short traces to minimize inductance. Capacitors can be placed directly under the device using a standard escape pattern. Others can surround the part.

These capacitors should have a value of 0.01 or 0.1 μ F. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, distribute several bulk storage capacitors around the PCB, feeding the V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors are 100–330 μ F (AVX TPS tantalum or Sanyo OSCON).

21.4 Connection Recommendations

To ensure reliable operation, connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD} , GV_{DD} , or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD} , GV_{DD} , LV_{DD} , OV_{DD} , and GND pins of the MPC8347E.

21.5 Output Buffer DC Impedance

The MPC8347E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 43). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

Revision	Date	Substantive Change(s)
8	2/2007	 Page 1, updated first paragraph to reflect PowerQUICC II information. Updated note after second paragraph. In the features list in Section 1, "Overview," corrected DDR data rate to show: 266 MHz for PBGA parts for all silicon revisions 333 MHz for DDR for TBGA parts for silicon Rev. 1.x
		In Table 5, "MPC8347E Typical I/O Power Dissipation," added GV _{DD} 1.8-V values for DDR2; added table footnote to designate rates that apply only to the TBGA package. In Figure 43, "JTAG Interface Connection," updated with new figure.
		In Section 23, "Ordering Information," replicated note from document introduction.
		In Section 23.1, "Part Numbers Fully Addressed by This Document," replaced third sentence of first paragraph directing customer to product summary page for available frequency configuration parts. Updated back page information.
7	8/2006	Changed all references to revision 2.0 silicon to revision 3.0 silicon. Changed V _{IH} minimum value in Table 36, "JTAG Interface DC Electrical Characteristics," to
		OV _{DD} – 0.3.
		In Table 60, "Suggested PLL Configurations," deleted reference-number rows 902 and 703.
6	3/2006	 Section 2, "Electrical Characteristics," moved to second section and all other section, table, and figure numbering change accordingly. Table 7, "CLKIN AC Timing Specifications:" Changed max rise and fall time from 1.2 to 2.3. Table 22, "GMII Receive AC Timing Specifications:" Changed min t_{TTKHDX} from 0.5 to 1.0. Table 30, "MII Management AC Timing Specifications:" Changed max value of t_{MDKHDX} from 70 to
		 170. Table 34, "Local Bus General Timing Parameters—DLL on:" Changed min t_{LBIVKH2} from 1.7 to 2.2. Table 36, "JTAG interface DC Electrical Characteristics:" Changed V_{IH} input high voltage min to 2.0. Table 54, "Operating Frequencies for TBGA:"
		 Updated TBD values. Changed maximum coherent system bus frequency for TBGA 667-MHz device to 333 MHz. Table 55, "Operating Frequencies for PBGA:"
		 Updated TBD values. Changed PBGA maximum coherent system bus frequency to 266 MHz, and maximum DDR memory bus frequency to 133 MHz. Table 60, "Suggested PLL Configurations": Removed some values from suggested PLL
		configurations for reference numbers 902, 922, 903, and 923.
		Table 67, "Part Numbering Nomenclature": Updated TBD values in note 1. Added Table 68, "SVR Settings." Added Section 23.2, "Part Marking."
5	10/2005	In Table 57, updated AAVID 30x30x9.4 mm Pin Fin (natural convection) junction-to-ambient thermal resistance, from 11 to 10.
4	9/2005	Added Table 2, "MPC8347E Typical I/O Power Dissipation."
3	8/2005	Table 1: Updated values for power dissipation that were TBD in Revision 2.
2	5/2005	Table 1: Typical values for power dissipation are changed to TBD. Table 48: Footnote numbering was wrong. THERM0 should have footnote 9 instead of 8.

Table 66. Document Revision History (continued)